

DATA SHEET



PEMB2

PNP resistor-equipped double
transistor $R1 = 47 \text{ k}\Omega$, $R2 = 47 \text{ k}\Omega$

Product specification

2001 Sep 14

PNP resistor-equipped double transistor

R1 = 47 kΩ, R2 = 47 kΩ

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FEATURES

- 300 mW total power dissipation
- Very small 1.6 mm × 1.2 mm × 0.55 mm ultra thin package
- Excellent coplanarity due to straight leads
- Reduces number of components as replacement of two SC-75/SC-89 packaged transistors
- Reduces required board space
- Reduces pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

DESCRIPTION

PNP resistor-equipped double transistor in a SOT666 plastic package.

MARKING

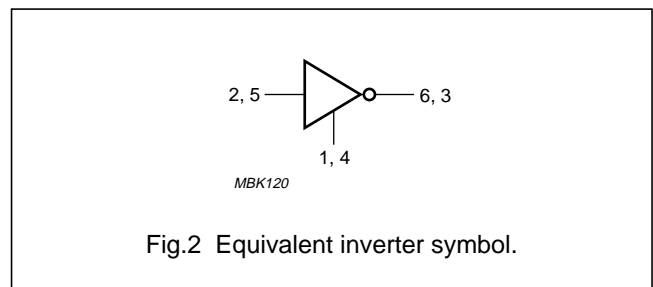
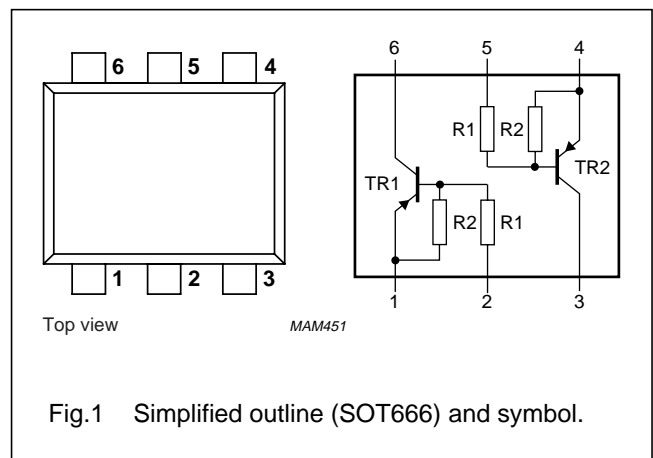
| TYPE NUMBER | MARKING CODE |
|-------------|--------------|
| PEMB2 | B2 |

PINNING

| PIN | DESCRIPTION |
|------|--------------------|
| 1, 4 | emitter TR1; TR2 |
| 2, 5 | base TR1; TR2 |
| 3, 6 | collector TR1; TR2 |

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | UNIT |
|------------------|---------------------------|------|------|
| V _{CEO} | collector-emitter voltage | -50 | V |
| I _{CM} | peak collector current | -100 | mA |
| TR1 | PNP | - | - |
| TR2 | PNP | - | - |
| R1 | bias resistor | 47 | kΩ |
| R2 | bias resistor | 47 | kΩ |



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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------------------|-------------------------------|---|------|------|------------------|
| Per transistor | | | | | |
| V_{CBO} | collector-base voltage | open emitter | – | –50 | V |
| V_{CEO} | collector-emitter voltage | open base | – | –50 | V |
| V_{EBO} | emitter-base voltage | open collector | – | –10 | V |
| V_I | input voltage | | | | |
| | positive | | – | +10 | V |
| | negative | | – | –40 | V |
| I_O | output current (DC) | | – | –100 | mA |
| I_{CM} | peak collector current | | – | –100 | mA |
| P_{tot} | total power dissipation | $T_{amb} \leq 25 \text{ }^\circ\text{C}$; note 1 | – | 200 | mW |
| T_{stg} | storage temperature | | –65 | +150 | $^\circ\text{C}$ |
| T_j | junction temperature | | – | 150 | $^\circ\text{C}$ |
| T_{amb} | operating ambient temperature | | –65 | +150 | $^\circ\text{C}$ |
| Per device | | | | | |
| P_{tot} | total power dissipation | $T_{amb} \leq 25 \text{ }^\circ\text{C}$; note 1 | – | 300 | mW |

Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|----------------------|---|--------------|-------|------|
| $R_{th \text{ j-a}}$ | thermal resistance from junction to ambient | note 1 and 2 | 416 | K/W |

Notes

1. Transistor mounted on an FR4 printed-circuit board.
2. The only recommended soldering method is reflow soldering.

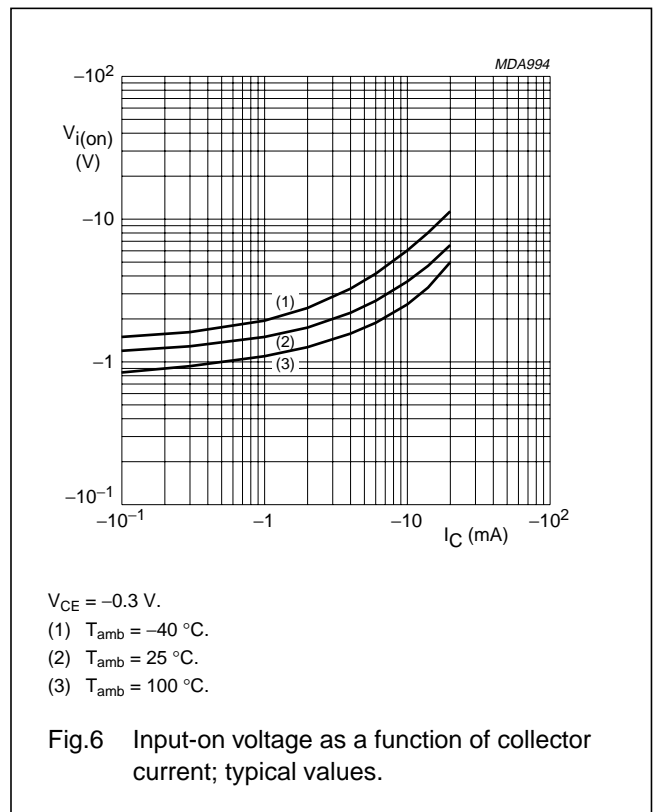
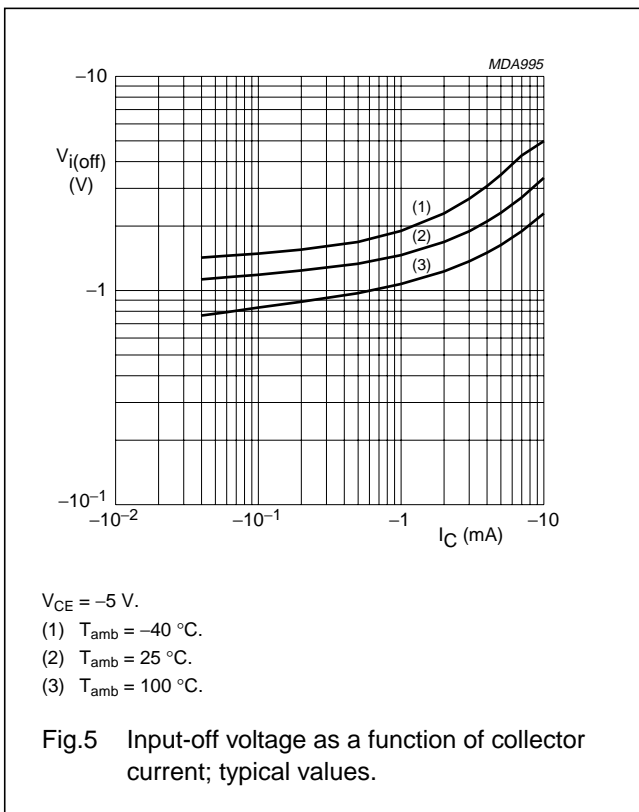
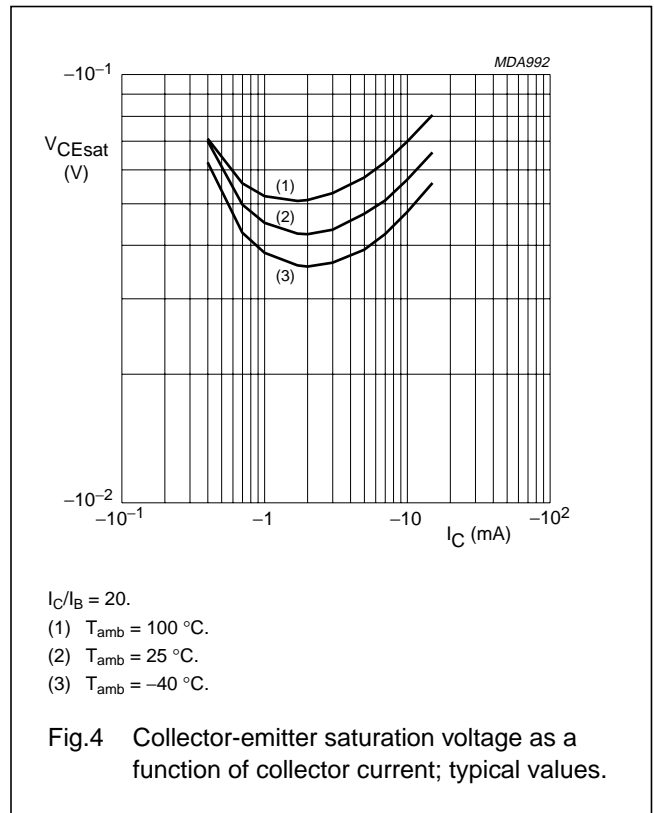
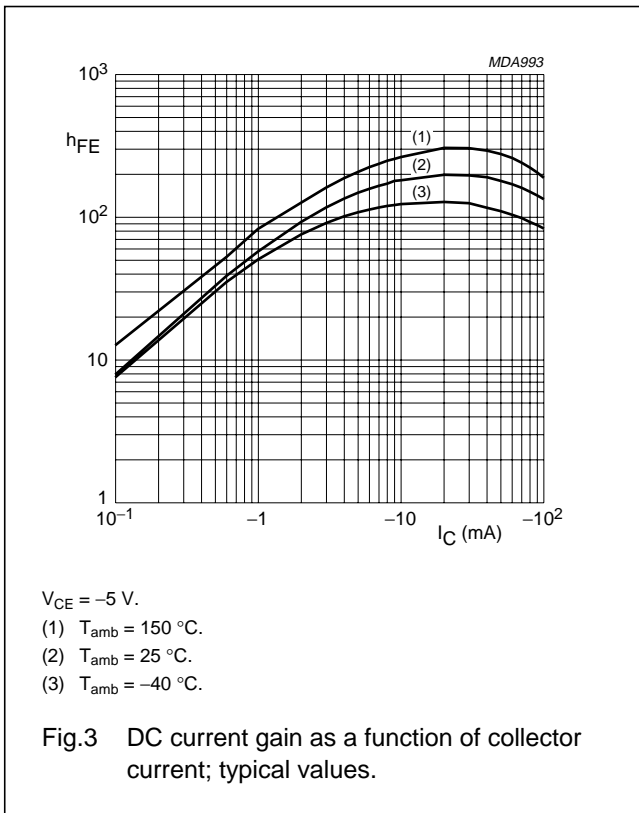
CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------------------|--------------------------------------|---|------|------|------|------------------|
| Per transistor | | | | | | |
| I_{CBO} | collector cut-off current | $I_E = 0$; $V_{CB} = -50 \text{ V}$ | – | – | –100 | nA |
| I_{CEO} | collector cut-off current | $I_B = 0$; $V_{CE} = -50 \text{ V}$ | – | – | –1 | μA |
| | | $I_B = 0$; $V_{CE} = -30 \text{ V}$; $T_j = 150 \text{ }^\circ\text{C}$ | – | – | –50 | μA |
| I_{EBO} | emitter cut-off current | $I_C = 0$; $V_{EB} = -5 \text{ V}$ | – | – | –90 | μA |
| h_{FE} | DC current gain | $I_C = -5 \text{ mA}$; $V_{CE} = -5 \text{ V}$ | 80 | – | – | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = -10 \text{ mA}$; $I_B = -0.5 \text{ mA}$ | – | – | –150 | mV |
| $V_{i(off)}$ | input-off voltage | $I_C = -100 \text{ }\mu\text{A}$; $V_{CE} = -5 \text{ V}$ | – | 1.2 | 0.8 | V |
| $V_{i(on)}$ | input-on voltage | $I_C = -2 \text{ mA}$; $V_{CE} = -0.3 \text{ V}$ | 3 | 1.6 | – | V |
| R1 | input resistor | | 33 | 47 | 61 | $\text{k}\Omega$ |
| $\frac{R2}{R1}$ | resistor ratio | | 0.8 | 1 | 1.2 | |
| C_c | collector capacitance | $I_E = I_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$ | – | – | 3 | pF |

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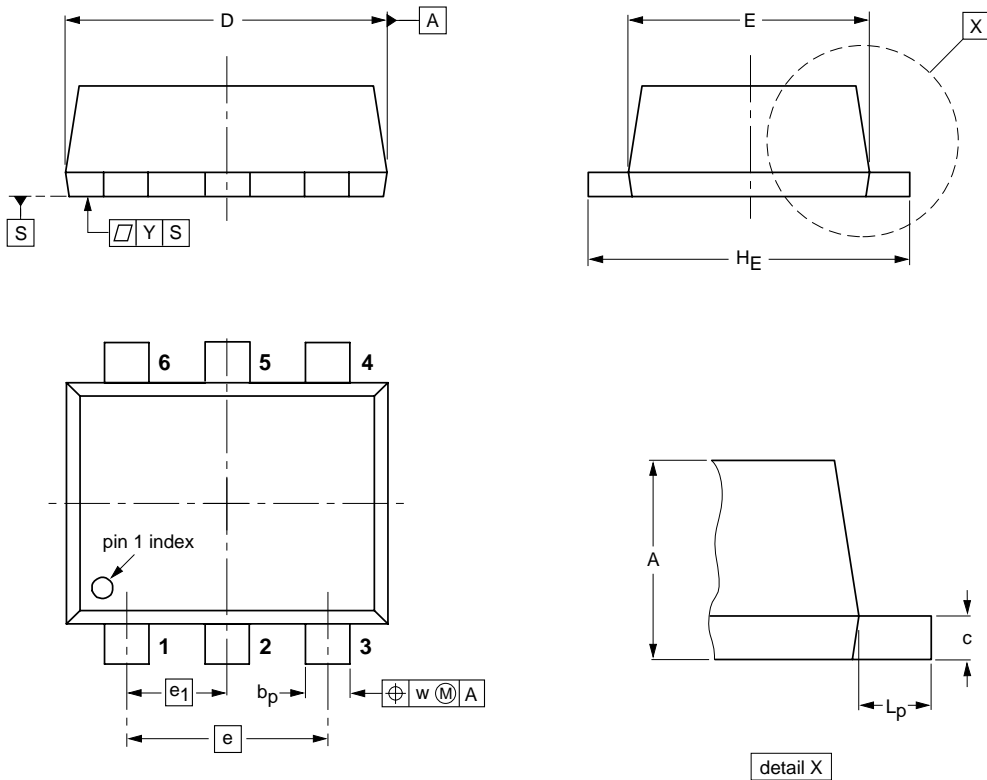
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



DIMENSIONS (mm are the original dimensions)

| UNIT | A | b_p | c | D | E | e | e_1 | H_E | L_p | w | y |
|------|------------|--------------|--------------|------------|------------|-----|-------|------------|------------|-----|-----|
| mm | 0.6 0.5 | 0.27 0.17 | 0.18 0.08 | 1.7 1.5 | 1.3 1.1 | 1.0 | 0.5 | 1.7 1.5 | 0.3 0.1 | 0.1 | 0.1 |

| OUTLINE VERSION | REFERENCES | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|------|---------------------|----------------------|
| | IEC | JEDEC | EIAJ | | |
| SOT666 | | | | | 01-01-04 01-08-27 |

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|----------------------------------|-------------------------------|--|
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Contact information

For additional information please visit <http://www.semiconductors.philips.com>. Fax: +31 40 27 24825

For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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